

High-reliability discrete products and engineering services since 1977

2N6077-2N6079

NPN SILICON HIGH POWER TRANSISTORS

NFEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Ratings	Symbol	2N6077	2N6078	2N6079	Unit
Collector-Emitter Voltage	V _{CEO}	275	250	350	Vdc
Collector-Base Voltage	V_{CBO}	300	275	375	Vdc
Emitter-Base Voltage	V_{EBO}		6.0		Vdc
Collector Current	lc		7.0		Adc
Total Power Dissipation T _C = 25°C	P_D		45		W
Junction Temperature	TJ		150		°C
Storage Junction Temperature Range	T_{stg}		-65 to +200		°C
Maximum Thermal Resistance Junction to Case	Rejc		4.28		°C/W

ELECTRICAL CHARACTERSITICS (T_A = 25°C unless otherwise specified)

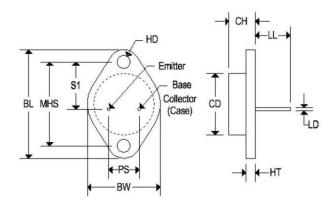
Characteristics		Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS		•			
Collector-Emitter Sustaining Voltage	2N6077		275	-	
$I_C = 10$ mA, $I_B = 0$	2N6078	V _{CEO(sus)}	250	-	Vdc
	2N6079		350	·	
Collector-Emitter Saturation Voltage		V			Vdc
$I_C = 5Adc$, $I_B = -0.5 Adc$		V _{CE(sat)}	-	1.0	vac
Collector-Base Saturation Voltage		V			Vdc
$I_C = 5Adc$, $I_B = -0.5 Adc$		V _{BE(sat)}	-	1.2	Vac
Collector Cutoff Current		,			0 -1 -
V_{CE} = Rated V_{CEO} , I_B = 0		ICEO	-	2.0	mAdc
Collector Cutoff Current					
V_{CE} = Rated V_{CEO} , $V_{BE(off)}$ = 1.5V		I _{CEO}	-	0.1	mAdc
V_{CE} = Rated V_{CEO} , $V_{BE(off)}$ = 1.5V, T_C = 125°C			-	1.0	
Collector Cutoff Current					0 -1 -
V_{CB} = Rated V_{CBO} , I_E = 0		Ісво	-	0.1	mAdc
Emitter Cutoff Current		,			0 -1 -
$V_{EB} = 6Vdc$, $I_C = 0$		I _{EBO}	-	1.0	mAdc
DC Current Gain		h			
$I_C = 1.2$ Adc, $V_{CE} = 1.0$ Vdc		h _{FE}	12	70	
Transition Frequency		f	7 /2		N.411-
$I_C = 500 \text{mAdc}$, $V_{CE} = 10 \text{Vdc}$, $f = 1 \text{MHz}$		f⊤	/ (1	yp)	MHz



High-reliability discrete products and engineering services since 1977

MECHANICAL CHARACTERISTICS

Case	TO-66
Marking	Alpha-numeric
Polarity	See below



2N6077-2N6079

NPN SILICON HIGH POWER TRANSISTORS

	TO-66					
Dim	Inc	hes	Millimeters			
	Min	Max	Min	Max		
BL	1.205	1.280	30.60	32.50		
CD	0.445	0.557	11.303	14.148		
СН	0.257	0.284	6.540	7.220		
LL	0.374	0.413	9.500	10.50		
BW	0.680	0.727	17.26	18.46		
LD	0.030	0.036	0.760	0.920		
HT	0.054	0.065	1.380	1.650		
MHS	0.951	0.976	24.16	24.78		
S1	0.545	0.614	13.84	15.60		
HD	0.131	0.154	3.320	3.920		
PS	0.191	0.210	4.860	5.340		